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November 2013

# FQPF5N90

# N-Channel QFET<sup>®</sup> MOSFET 900 V, 3 A, 2.3 $\Omega$

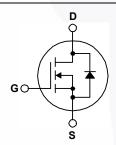
## **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### **Features**

- 3 A, 900 V,  $R_{DS(on)}$  = 2.3  $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 1.5 A
- Low Gate Charge (Typ. 31 nC)
- Low Crss (Typ. 13 pF)
- · 100% Avalanche Tested
- LoHS Compliant





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQPF5N90	Unit
$V_{DSS}$	Drain-Source Voltage	900	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	3.0	Α
	- Continuous (T <sub>C</sub> = 100°C)	1.9	Α
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	12	Α
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	660	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	3.0	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	5.1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)	51	W
	- Derate Above 25°C	0.41	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds	300	°C

# **Thermal Characteristics**

Symbol	Parameter FQPF5N		Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max. 62.5		C/VV

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF5N90	FQPF5N90	TO-220F	Tube	N/A	N/A	50 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	900			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		1.0		V/°C
I <sub>DSS</sub>	Zana Cata Maltana Dunin Courset	V <sub>DS</sub> = 900 V, V <sub>GS</sub> = 0 V			10	μА
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 720 V, T <sub>C</sub> = 125°C			100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A		1.8	2.3	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 1.5 A		4.0		S
	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1200	1550	pF
C <sub>oss</sub>	Output Capacitance	f = 1 MHz		110	145	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			13	17	pF
Switch	ing Characteristics	,				
		,		28	65	
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 450 V I <sub>D</sub> = 5.4 A				ns
t <sub>d(on)</sub>	Turn-On Delay Time Turn-On Rise Time	$V_{DD} = 450 \text{ V}, I_{D} = 5.4 \text{ A},$ $R_{C} = 25 \Omega$		65	140	ns ns
t <sub>r</sub>	·	$V_{DD}$ = 450 V, $I_{D}$ = 5.4 A, $R_{G}$ = 25 $\Omega$				
t <sub>r</sub>	Turn-On Rise Time			65	140	ns
t <sub>r</sub>	Turn-On Rise Time Turn-Off Delay Time	$R_G = 25 \Omega$		65 65	140 140	ns ns
t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time	$R_G$ = 25 Ω (Note 4)		65 65 50	140 140 110	ns ns ns

# **Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				3.0	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				12	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 3.0 \text{ A}$			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V, I}_{S} = 5.4 \text{ A,}$		610		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		5.26	-	μС

#### Notes

- 1. Repetitive rating: pulse width-limited by maximum junction temperature.
- 2. L = 139 mH, I  $_{AS}$  = 3.0 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\Omega,$  starting  $\,$  T  $_{J}$  = 25  $^{\circ}C.$
- 3.  $I_{SD} \le$  5.4 A, di/dt  $\le$  200 A/ $\mu$ s,  $V_{DD} \le$  BV $_{DSS}$ , starting  $T_J$  = 25°C.
- Essentially independent of operating temperature.

# **Typical Characteristics**

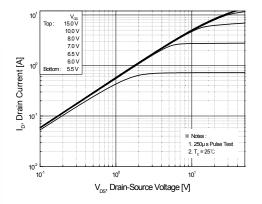


Figure 1. On-Region Characteristics

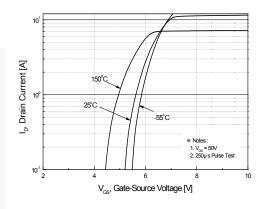


Figure 2. Transfer Characteristics

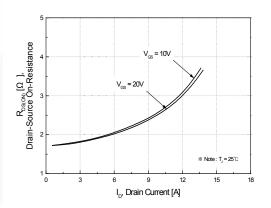


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

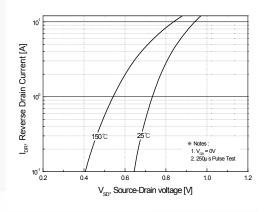


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

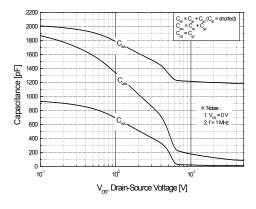


Figure 5. Capacitance Characteristics

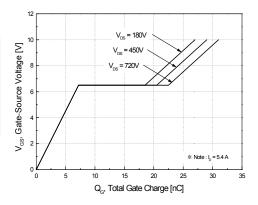
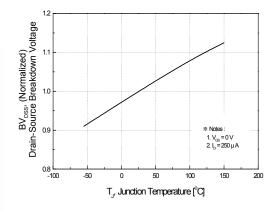


Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)



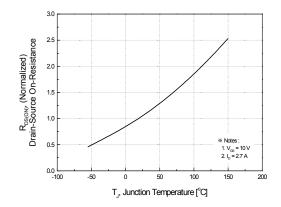
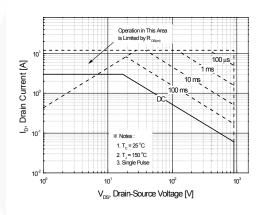


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



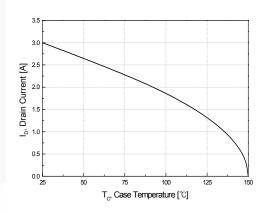


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

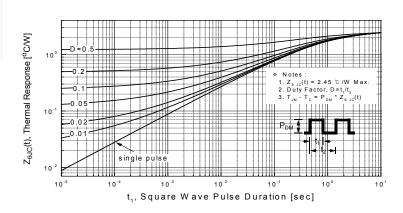


Figure 11. Transient Thermal Response Curve

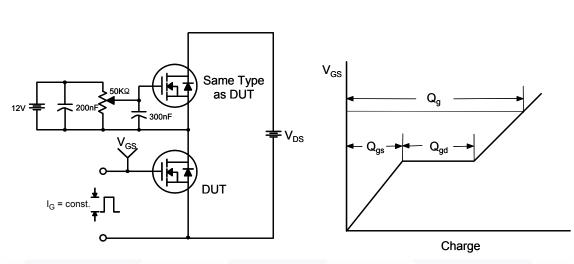


Figure 12. Gate Charge Test Circuit & Waveform

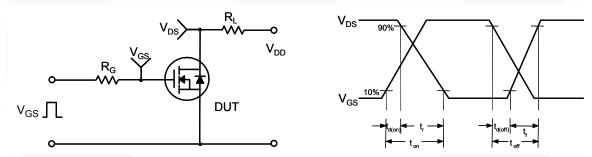


Figure 13. Resistive Switching Test Circuit & Waveforms

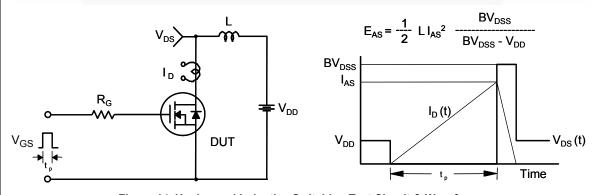
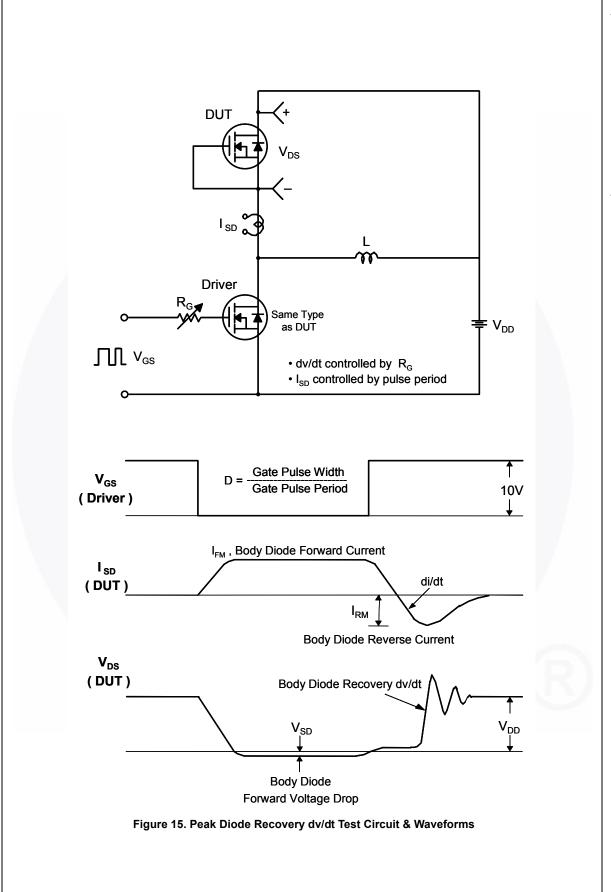


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

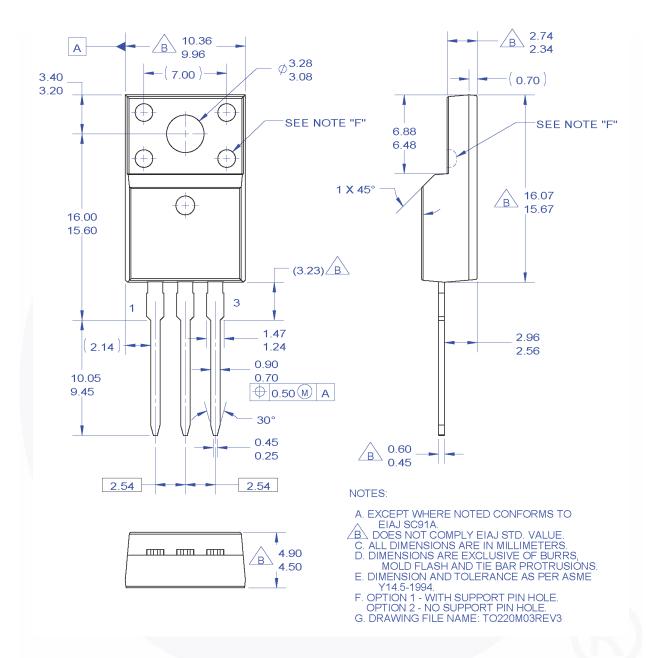


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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